



6N70K-MT

Power MOSFET

6.0A, 700V N-CHANNEL POWER MOSFET

DESCRIPTION

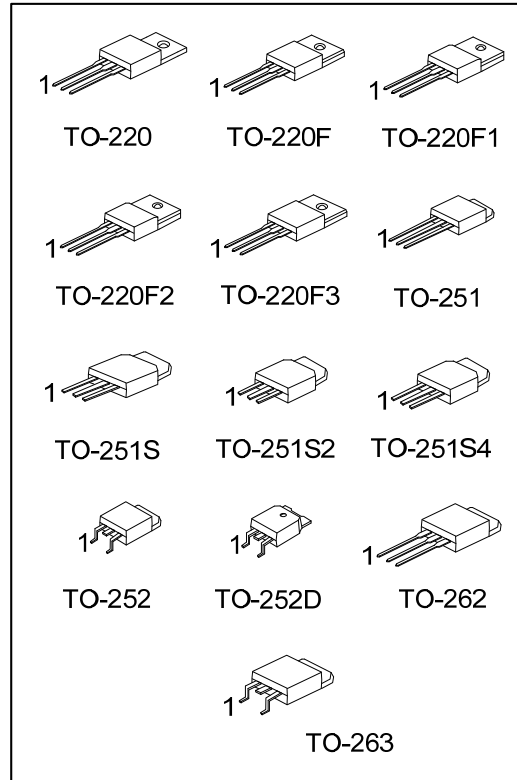
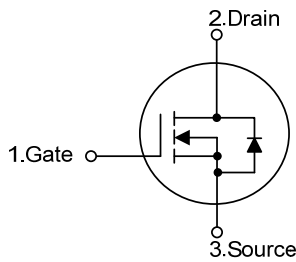
The UTC **6N70K-MT** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with a minimum on-state resistance, high switching speed, low gate charge and low input capacitance.

The UTC **6N70K-MT** is universally applied in high efficiency switch mode power supply.

FEATURES

- * $R_{DS(ON)} \leq 1.6 \Omega @ V_{GS}=10V, I_D=3.0A$
- * High switching speed

SYMBOL



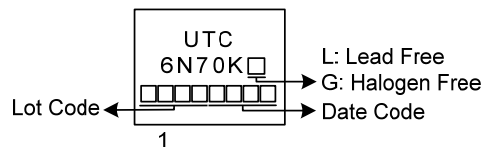
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
6N70KL-TA3-T	6N70KG-TA3-T	TO-220	G	D	S	Tube
6N70KL-TF3-T	6N70KG-TF3-T	TO-220F	G	D	S	Tube
6N70KL-TF1-T	6N70KG-TF1-T	TO-220F1	G	D	S	Tube
6N70KL-TF2-T	6N70KG-TF2-T	TO-220F2	G	D	S	Tube
6N70KL-TF3T-T	6N70KG-TF3T-T	TO-220F3	G	D	S	Tube
6N70KL-TM3-T	6N70KG-TM3-T	TO-251	G	D	S	Tube
6N70KL-TMS-T	6N70KG-TMS-T	TO-251S	G	D	S	Tube
6N70KL-TMS2-T	6N70KG-TMS2-T	TO-251S2	G	D	S	Tube
6N70KL-TMS4-T	6N70KG-TMS4-T	TO-251S4	G	D	S	Tube
6N70KL-TN3-R	6N70KG-TN3-R	TO-252	G	D	S	Tape Reel
6N70KL-TND-R	6N70KG-TND-R	TO-252D	G	D	S	Tape Reel
6N70KL-T2Q-T	6N70KG-T2Q-T	TO-262	G	D	S	Tube
6N70KL-TQ2-T	6N70KG-TQ2-T	TO-263	G	D	S	Tube
6N70KL-TQ2-R	6N70KG-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>6N70KG-TA3-T</p> <p>(1) Packing Type</p> <p>(2) Package Type</p> <p>(3) Green Package</p>	<p>(1) T: Tube, R: Tape Reel</p> <p>(2) TA3: TO-220, TF1: TO-220F1, TF2: TO-220F2, TF3: TO-220F, TF3T: TO-220F3, TM3: TO-251, TMS: TO-251S, TMS2: TO-251S2, TN3: TO-252, TMS4: TO-251S4, TND: TO-252D, T2Q: TO-262, TQ2: TO-263</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V_{DSS}	700	V	
Gate-Source Voltage (Note 2)		V_{GSS}	± 30	V	
Drain Current	Continuous	I_D	$T_C=25^\circ\text{C}$	6	A
			$T_C=100^\circ\text{C}$	3.8	A
Pulsed		I_{DM}	24	A	
Avalanche Current (Note 2)		I_{AR}	6	A	
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	284	mJ	
	Repetitive (Note 2)	E_{AR}	13	mJ	
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.5	V/ns	
Power Dissipation	TO-220/TO-263	P_D	125	W	
	TO-220F		32	W	
	TO-220F1/TO-220F2		33	W	
	TO-220F3				
	TO-251/TO-251S		48	W	
	TO-251S2/TO-251S4				
TO-252/TO-252D					
TO-262		125	W		
Junction Temperature		T_J	+150	$^\circ\text{C}$	
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3. $L = 15.77\text{mH}$, $I_{AS} = 6.0\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 27\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 6.0\text{A}$, $di/dt \leq 140\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2 TO-220F3/TO-262 TO-263	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D		110	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220	θ_{JC}	1	$^\circ\text{C}/\text{W}$
	TO-220F		3.9	$^\circ\text{C}/\text{W}$
	TO-220F1/TO-220F2 TO-220F3		3.78	$^\circ\text{C}/\text{W}$
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D		2.6 (Note)	$^\circ\text{C}/\text{W}$
	TO-262		1	$^\circ\text{C}/\text{W}$

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

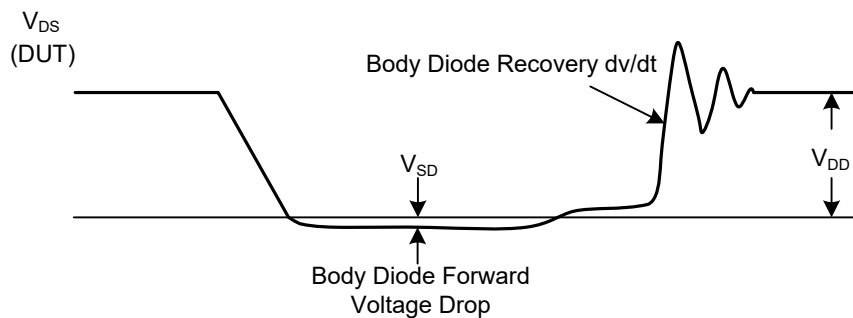
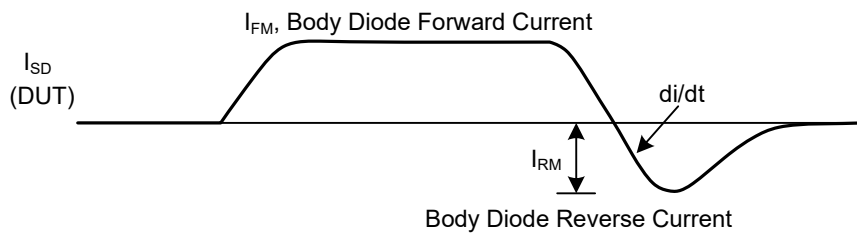
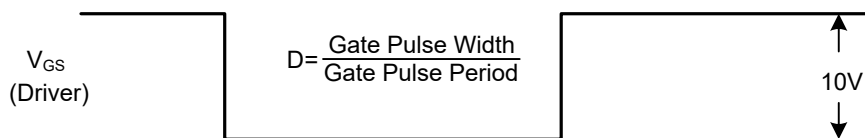
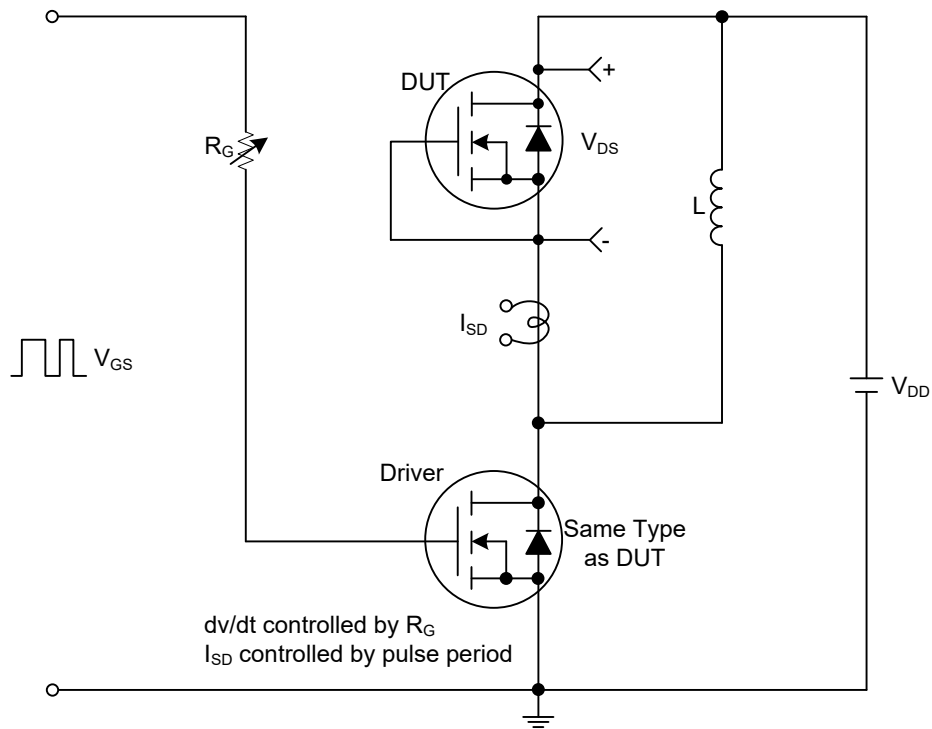
■ ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	700			V
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D=250\mu\text{A}$		0.79		V/ $^\circ\text{C}$
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=700\text{V}$			25	μA
		$V_{DS}=560\text{V}$, $T_C=125^\circ\text{C}$			250	μA
Gate-Source Leakage Current	Forward	$V_{GS}=+30\text{V}$, $V_{DS}=0\text{V}$			+100	nA
	Reverse	$V_{GS}=-30\text{V}$, $V_{DS}=0\text{V}$			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=3.0\text{A}$ (Note 1)		1.35	1.6	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$, $f=1.0\text{MHz}$ (Note 1, 2)		480	600	pF
Output Capacitance	C_{OSS}			80	100	pF
Reverse Transfer Capacitance	C_{RSS}			6.5	25	pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	$V_{DS}=50\text{V}$, $V_{GS}=10\text{V}$, $I_D=1.3\text{A}$ $I_G=100\mu\text{A}$ (Note 1, 2)		21.8	32	nC
Gate to Source Charge	Q_{GS}			6.8		nC
Gate to Drain Charge	Q_{GD}			4.8		nC
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD}=30\text{V}$, $V_{GS}=10\text{V}$, $I_D=0.5\text{A}$, $R_G=25\Omega$ (Note 1, 2)		57	80	ns
Rise Time	t_R			60	85	ns
Turn-OFF Delay Time	$t_{D(OFF)}$			130	140	ns
Fall-Time	t_F			54	60	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S	Integral reverse pn-diode in the MOSFET			6	A
Maximum Body-Diode Pulsed Current (Note 3)	I_{SM}				24	A
Drain-Source Diode Forward Voltage (Note 2)	V_{SD}	$I_S=6\text{A}$, $V_{GS}=0\text{V}$, $T_J = 25^\circ\text{C}$			1.4	V
Reverse Recovery Time	t_{rr}	$I_S=6\text{A}$, $V_{DD}=100\text{V}$		480		ns
Reverse Recovery Charge	Q_{rr}	$di/dt = 100\text{A}/\mu\text{s}$		3.5		μC

Notes: 1. Pulse Test: Pulse width $\leq 250\mu\text{s}$, Duty cycle $\leq 2\%$.

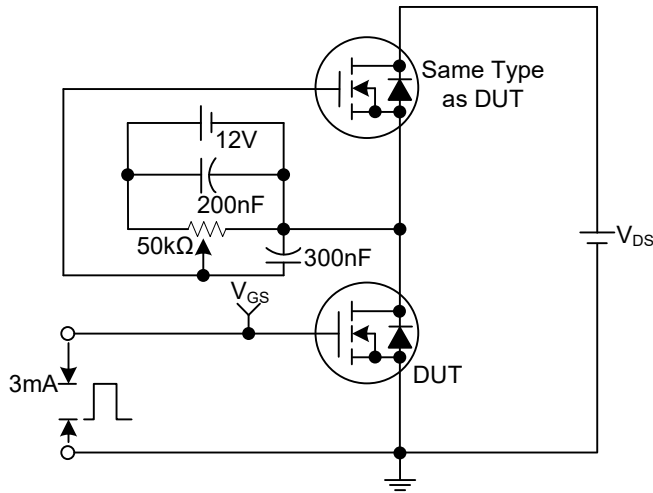
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

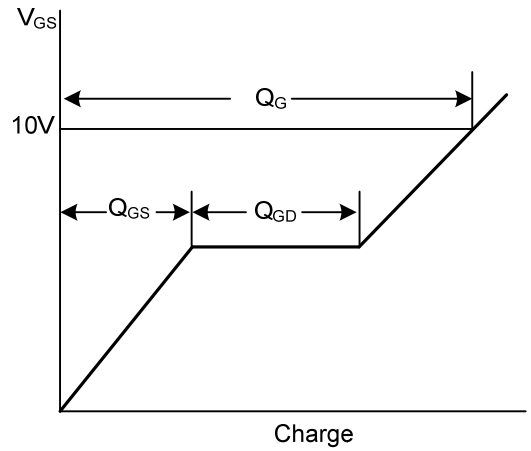


Peak Diode Recovery dv/dt Test Circuit and Waveforms

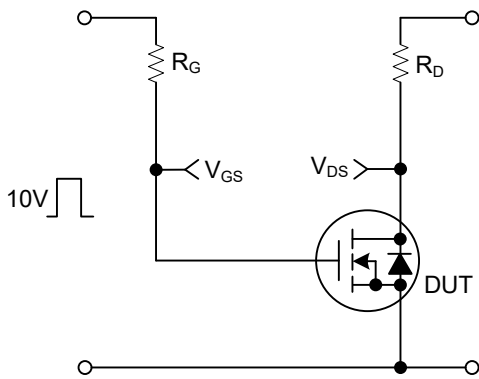
TEST CIRCUITS AND WAVEFORMS



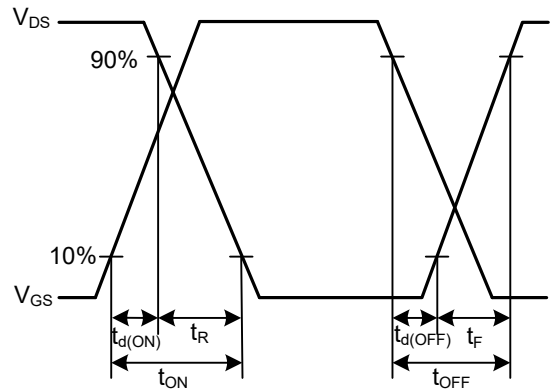
Gate Charge Test Circuit



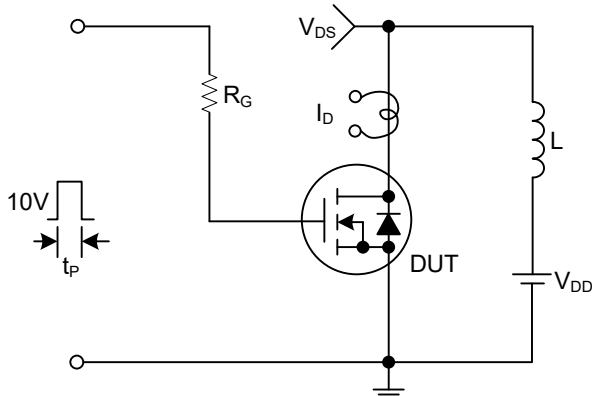
Gate Charge Waveforms



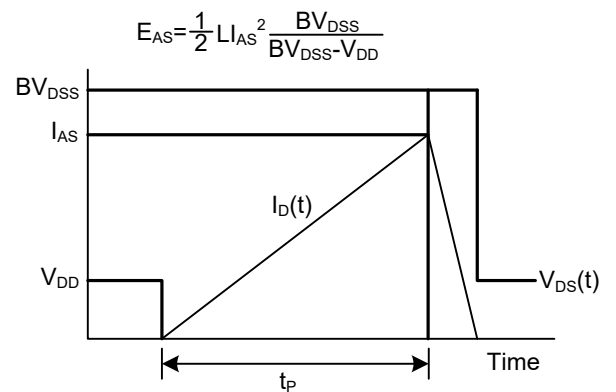
Resistive Switching Test Circuit



Resistive Switching Waveforms

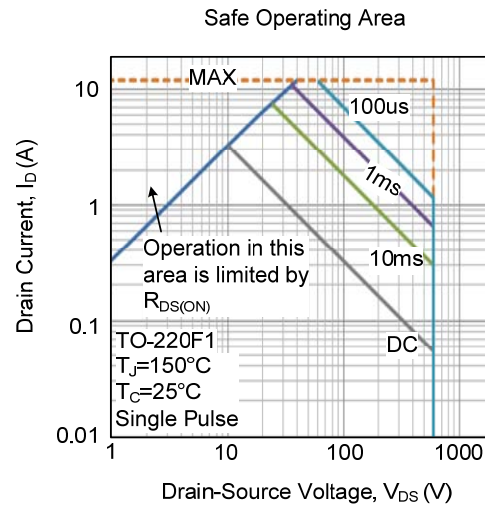
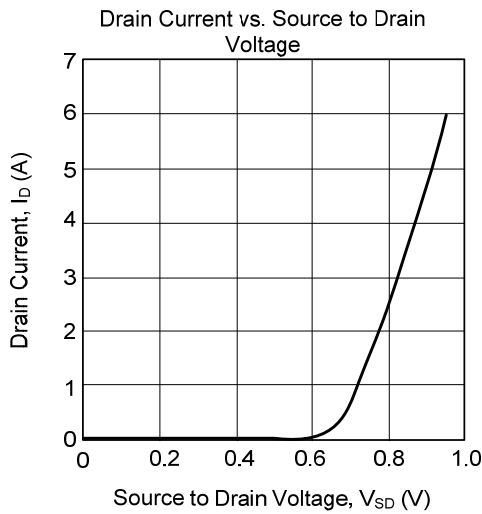


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS



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